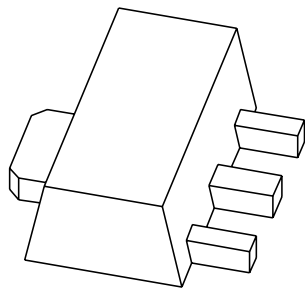


DATA SHEET



PDF.Support

BCX54; BCX55; BCX56 NPN medium power transistors

Product specification
Supersedes data of 1999 Apr 19

2001 Oct 10

NPN medium power transistors

BCX54; BCX55; BCX56

FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V).

APPLICATIONS

- Driver stages of audio and video amplifiers.

DESCRIPTION

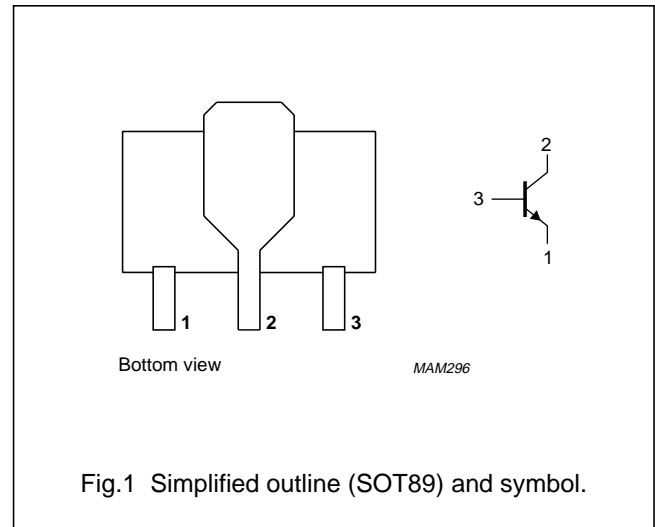
NPN medium power transistor in a SOT89 plastic package. PNP complements: BCX51, BCX52 and BCX53.

MARKING

TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE
BCX54	BA	BCX55-16	BM
BCX54-10	BC	BCX56	BH
BCX54-16	BD	BCX56-10	BK
BCX55	BE	BCX56-16	BL
BCX55-10	BG		

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base



NPN medium power transistors

BCX54; BCX55; BCX56

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BCX54		–	45	V
	BCX55		–	60	V
	BCX56	–	100	V	
V _{CEO}	collector-emitter voltage	open base			
	BCX54		–	45	V
	BCX55		–	60	V
	BCX56	–	80	V	
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	1	A
I _{CM}	peak collector current		–	1.5	A
I _{BM}	peak base current		–	0.2	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	1.3	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

- Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 6 cm².
For other mounting conditions, see *“Thermal considerations for SOT89 in the General Part of associated Handbook”*.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	94	K/W
R _{th j-s}	thermal resistance from junction to soldering point		14	K/W

Note

- Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 6 cm².
For other mounting conditions, see *“Thermal considerations for SOT89 in the General Part of associated Handbook”*.

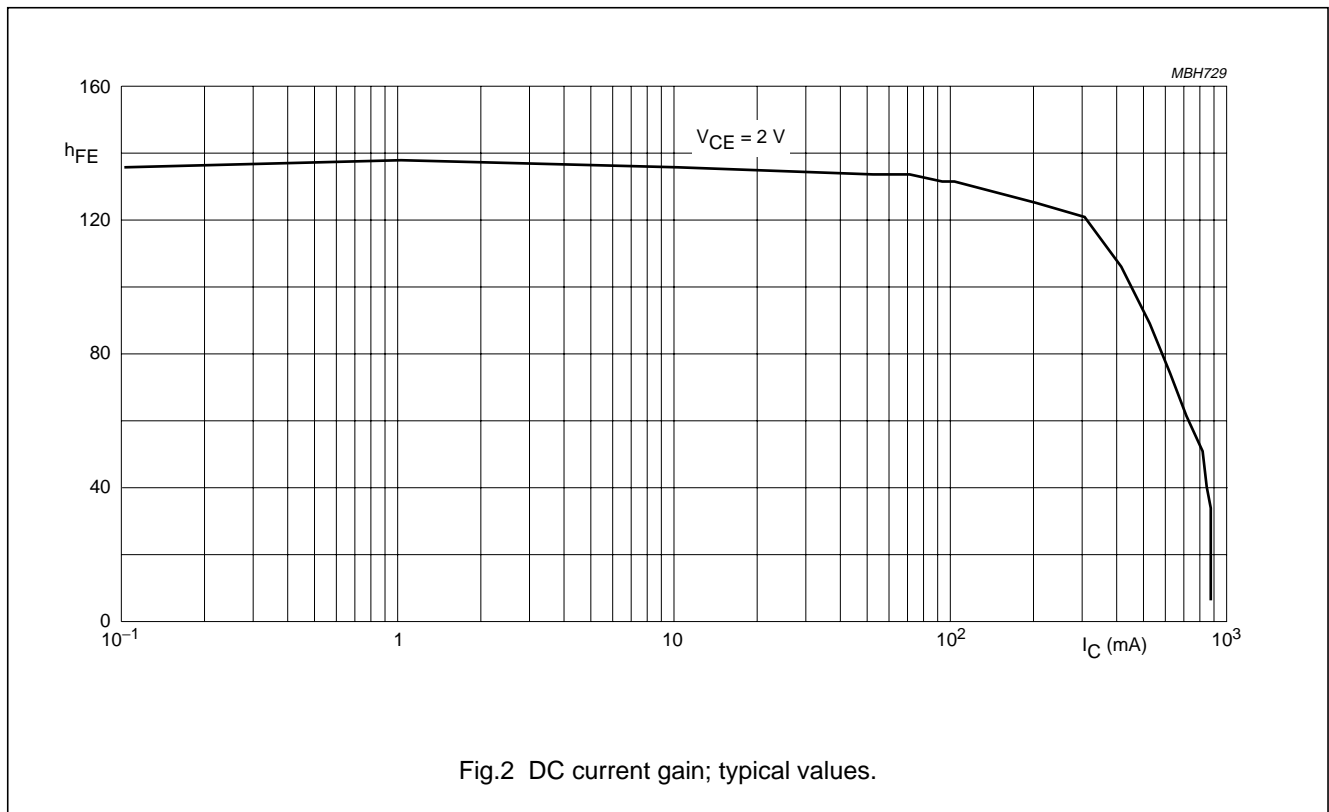
NPN medium power transistors

BCX54; BCX55; BCX56

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 30 V	–	–	100	nA
		I _E = 0; V _{CB} = 30 V; T _j = 125 °C	–	–	10	μA
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 5 V	–	–	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; (see Fig.2)				
		I _C = 5 mA	63	–	–	
		I _C = 150 mA	63	–	250	
	I _C = 500 mA	40	–	–		
DC current gain	I _C = 150 mA; V _{CE} = 2 V; (see Fig.2)					
	BCX54-10; 55-10; 56-10	63	–	160		
	BCX54-16; 55-16; 56-16	100	–	250		
V _{CEsat}	collector-emitter saturation voltage	I _C = 500 mA; I _B = 50 mA	–	–	0.5	V
V _{BE}	base-emitter voltage	I _C = 500 mA; V _{CE} = 2 V	–	–	1	V
f _T	transition frequency	I _C = 10 mA; V _{CE} = 5 V; f = 100 MHz	–	130	–	MHz
$\frac{h_{FE1}}{h_{FE2}}$	DC current gain ratio of the complementary pairs	I _C = 150 mA; V _{CE} = 2 V	–	1.3	1.6	



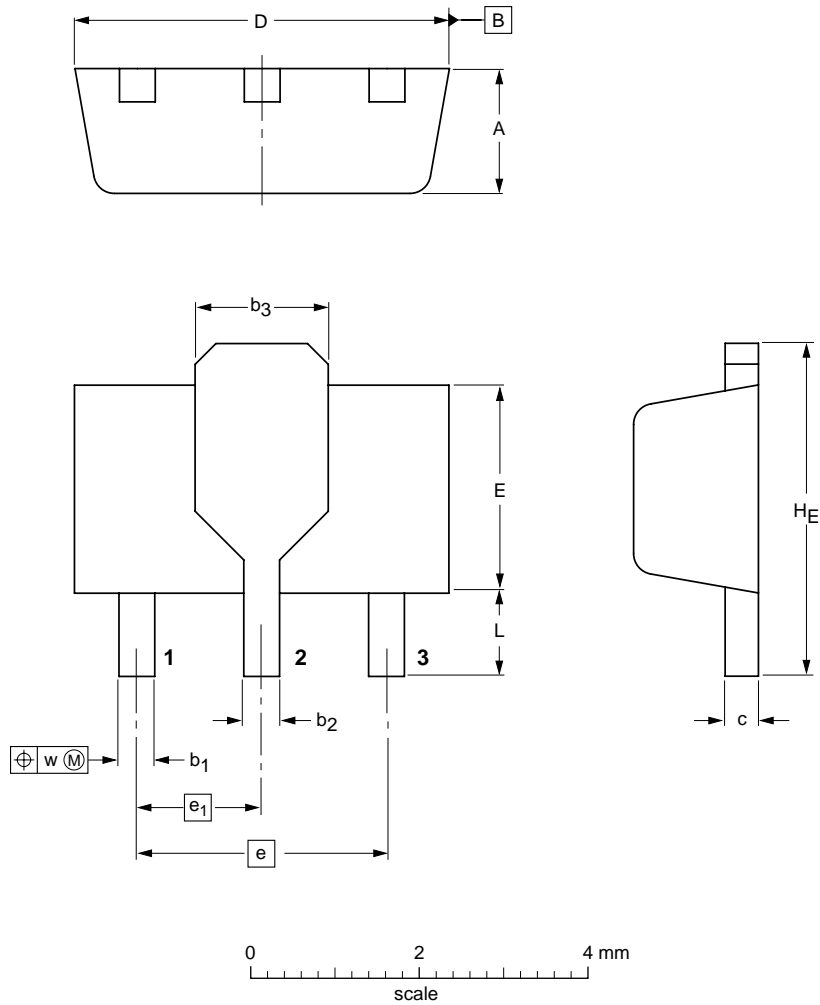
NPN medium power transistors

BCX54; BCX55; BCX56

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b ₁	b ₂	b ₃	c	D	E	e	e ₁	H _E	L min.	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.37	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	0.8	0.13

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT89		TO-243	SC-62			97-02-28 99-09-13

NPN medium power transistors

BCX54; BCX55; BCX56

DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

Notes

1. Please consult the most recently issued data sheet before initiating or completing a design.
2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

DISCLAIMERS

Life support applications — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes, without notice, in the products, including circuits, standard cells, and/or software, described or contained herein in order to improve design and/or performance. Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no licence or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

NPN medium power transistors

BCX54; BCX55; BCX56

NOTES

Philips Semiconductors – a worldwide company

Contact information

For additional information please visit <http://www.semiconductors.philips.com>. Fax: +31 40 27 24825

For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

© Koninklijke Philips Electronics N.V. 2001

SCA73

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

613514/04/pp8

Date of release: 2001 Oct 10

Document order number: 9397 750 08744

Let's make things better.

**Philips
Semiconductors**



PHILIPS